FIG. 1

FIG. 2

THICKNESS OF CHEMICAL OXIDE FILM ON SILICON WAFER SURFACE (nm)
TREATMENT TIME WITH OZONIZED WATER (sec)

FIG. 3

SC-1 CLEANING

OZONIZED WATER TREATMENT + HYDROFLUORIC ACID CLEANING EXISTENCE RATIO OF Si ATOM COORDINATION NUMBER (%)
TIME PASSAGE SINCE CLEANING (hr)

FIG. 4

FIG. 5

HYDROGEN ANNEALING

OZONIZED WATER/HF CLEANING

SC-1 CLEANING

SPATIAL FREQUENCY (/µm)

FIG. 6

HYDROGEN ANNEALING

OZONIZED WATER CLEANING

EXTRAPURE WATER CLEANING

SPATIAL FREQUENCY (/µm)

Title: SILICON WAFER
CLEANING METHOD
Inventor(s): Hisatsugu KURITA et al.
DOCKET NO.: 047297-0137

Fig.1

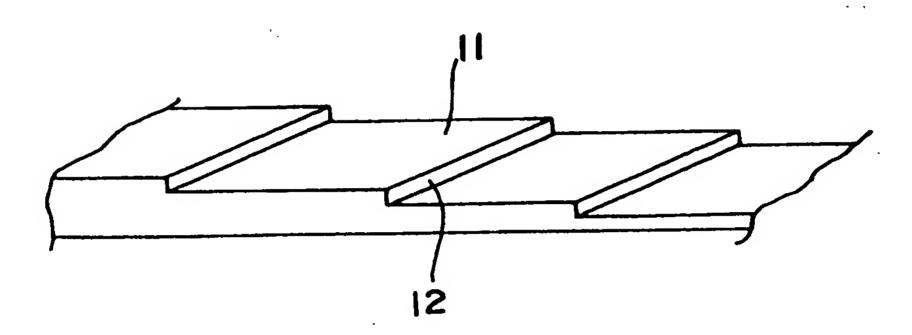
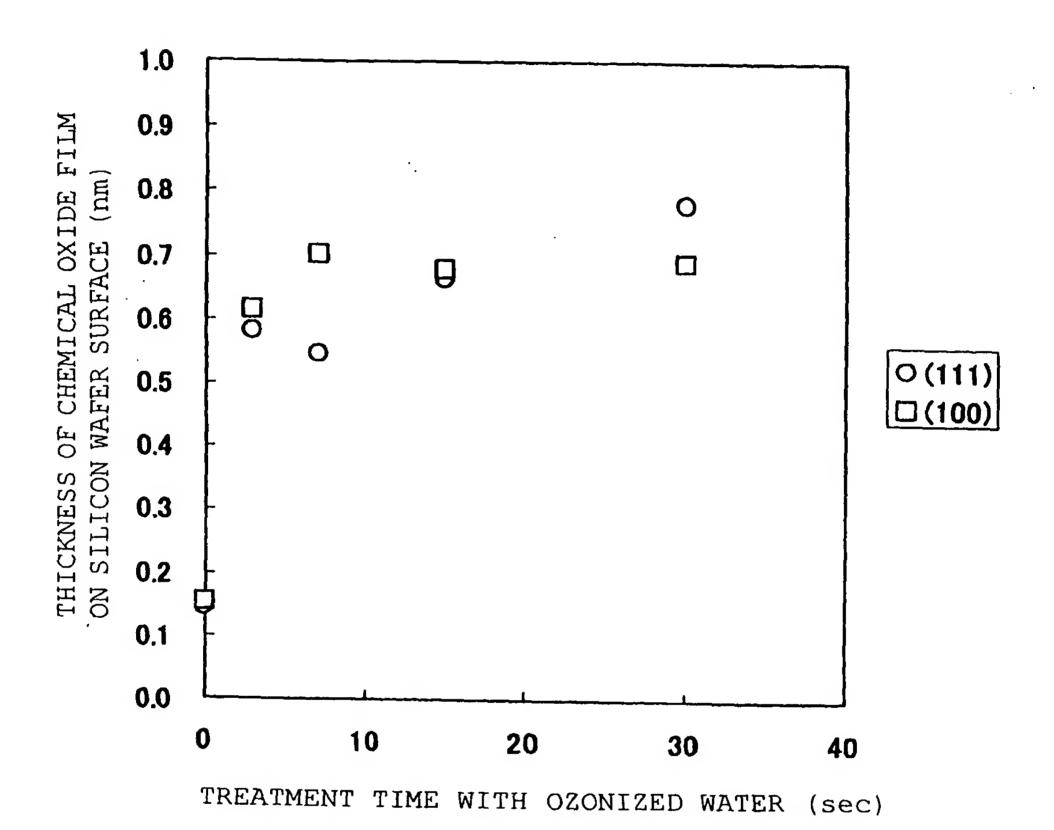
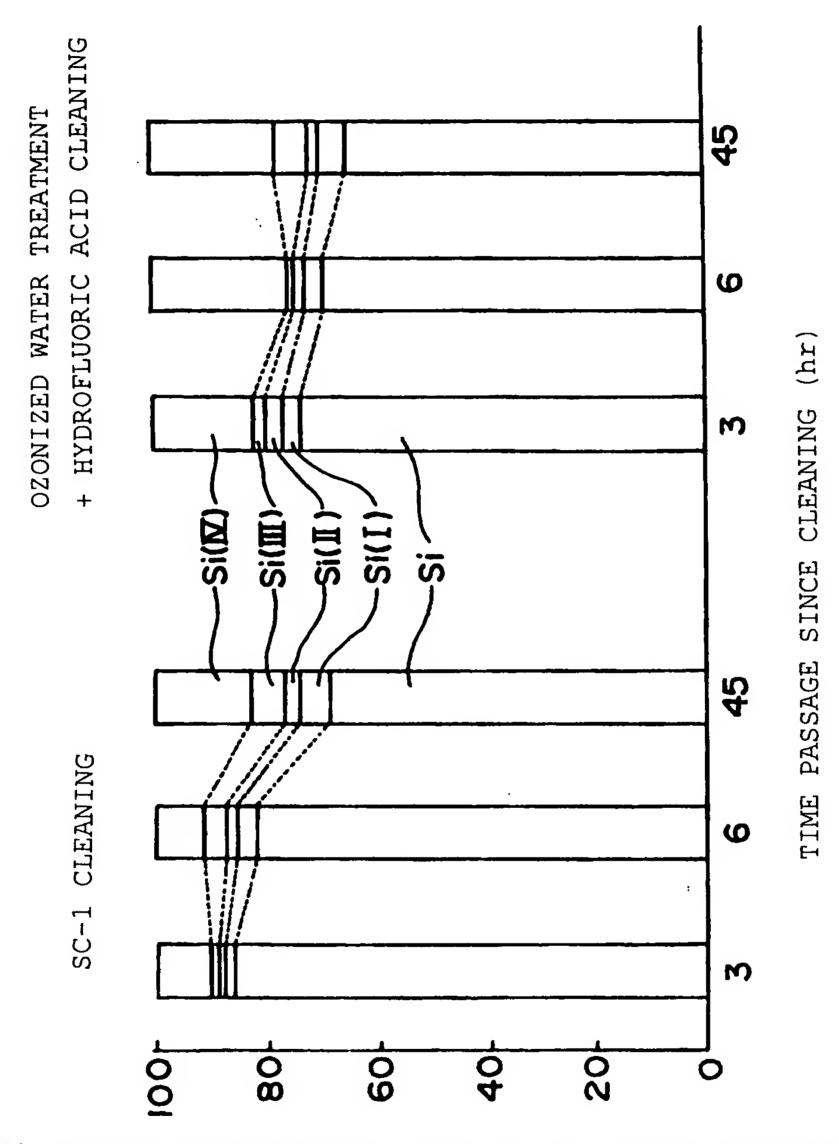


Fig.2



Title: SILICON WAFER
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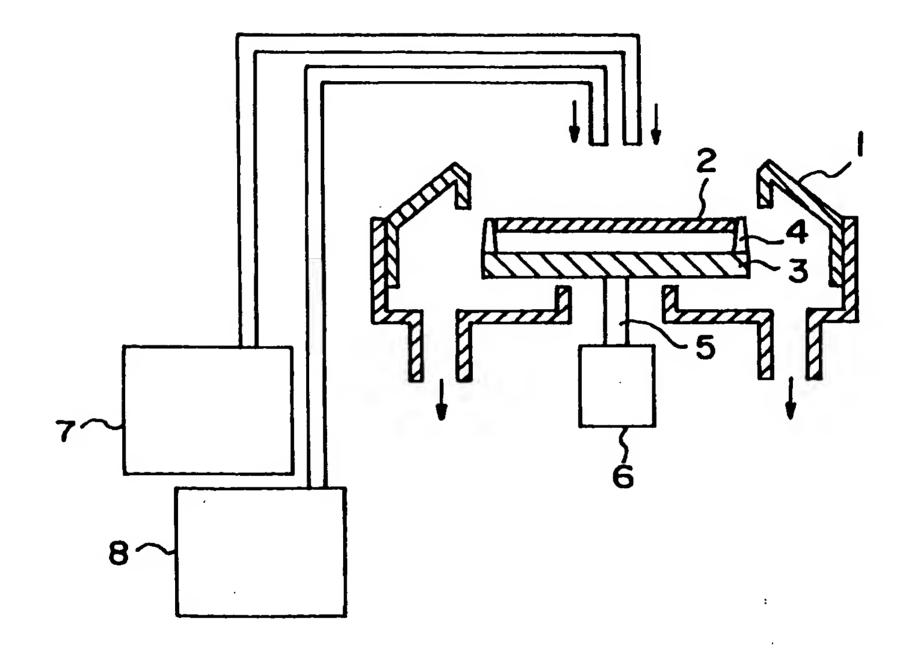
Fig.3

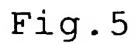


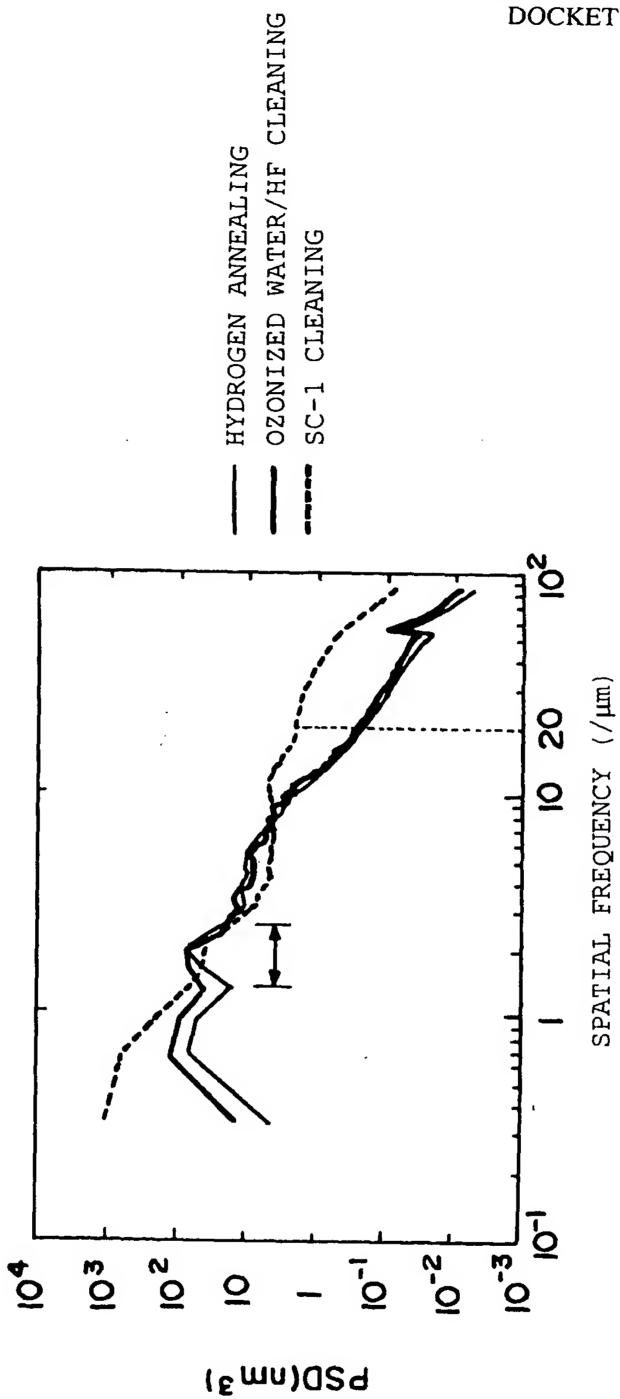
EXISTENCE RATIO OF SI ATOM COORDINATION NUMBER (%)

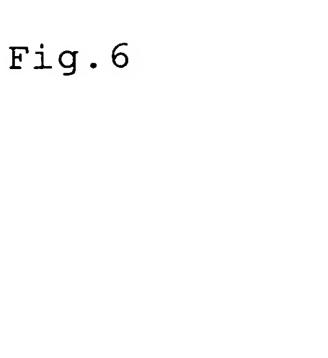
Title: SILICON WAFER
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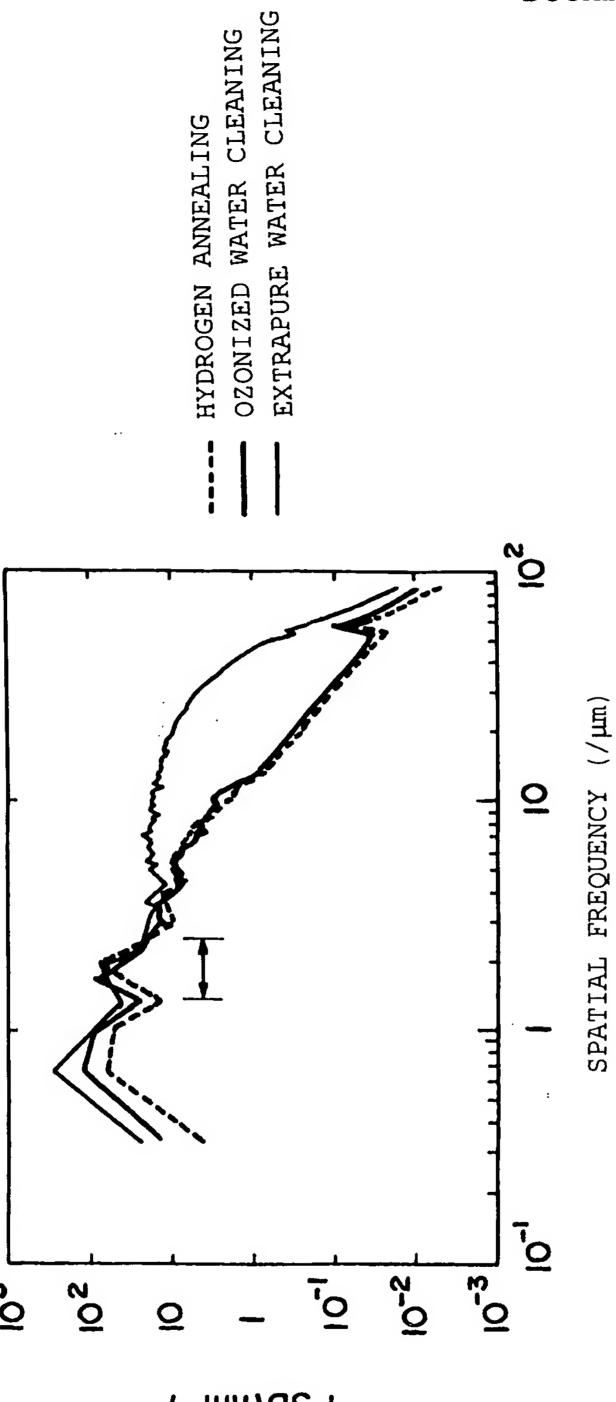
Fig.4











PSD(nm³)